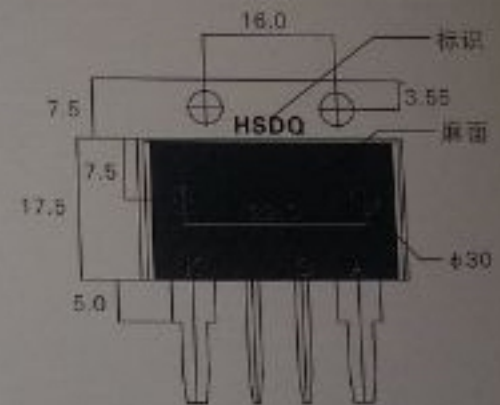
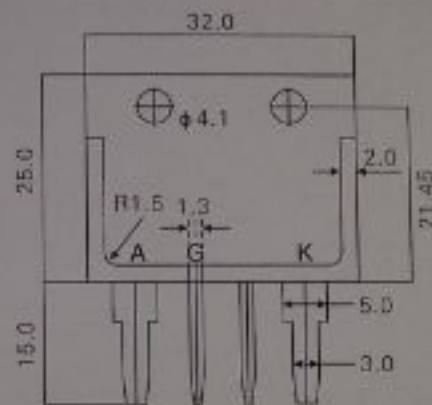
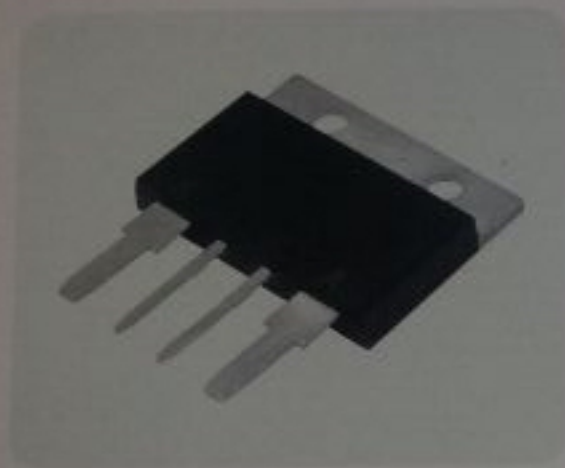


功率半导体器件



BT80双向可控硅

特点: 先进的玻璃钝化工艺, 灵敏的控制极触发电流, 较低的通态压降, 通过ROHS认证。

用途: 用于各种万能开关器、小型马达控制器、彩灯控制器、漏电保护器、逻辑集成电路驱动、摩托车点火器等电路中。

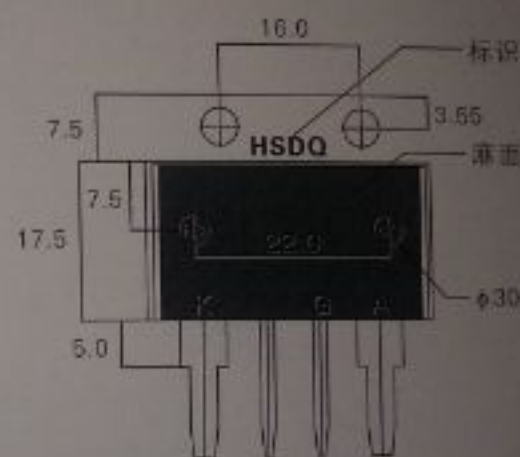
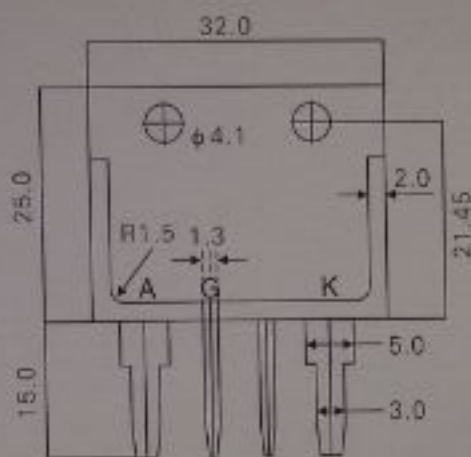
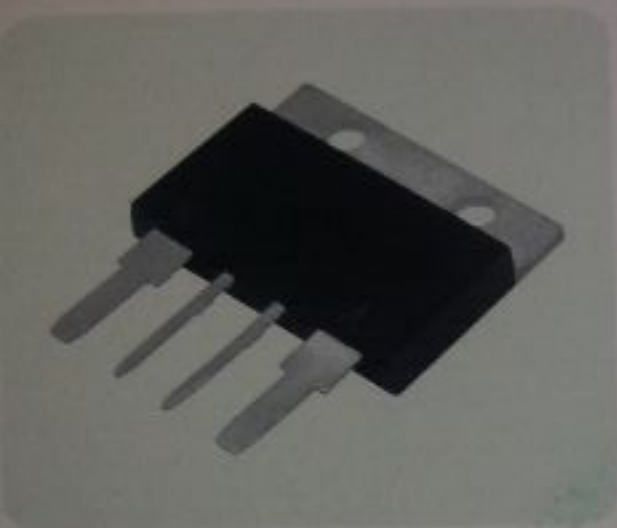
极限值

参数名称	符号	规范值	单位
断态重复峰值断电压	V_{DRM}	≥ 800	V
反向重复峰值断电压	V_{RRM}	≥ 800	V
通态方均根电流	$I_{T(RMS)}$	80	A
通态浪涌电流	I_{TSM}	800	A
工作结温	T_j	-40 ~ 125	$^{\circ}\text{C}$
贮存温度	T_{stg}	-40 ~ 150	$^{\circ}\text{C}$

电特性($T_j=25^{\circ}\text{C}$)

参数名称	符号	规范值	单位	测试条件	
通态峰值电压	V_{TM}	1.50	V	$I_T=120\text{A}$	
断态重复峰值电流	I_{DRM}	≤ 1.5	mA	$V_{DRM}=800\text{V}$	
门极触发电流	I_{GT}	T2+G+	≤ 50	mA	$V_{DRM}=12\text{V}$ $R_L=10\Omega$
		T2+G-	≤ 50		
		T2-G-	≤ 50		
		T2-G+	≤ 80		
门极触发电压	V_{GT}	≤ 1.3	V	$V_D=12\text{V}$ $R_L=10\Omega$	
维持电流	I_H	80	mA		
断态电压临界上升率	dv/dt	≥ 500	V/ μS		

Power semiconductor devices



BT80 two-way controllable silicon

Characteristics: advanced glass passivated device, sensitive control pole triggering current, relatively low on-state voltage drop and passed ROHS certification.

Purpose: used in circuits of various motor speed controllers, small-size motor controller, color light controller, leakage protector, driving of logic integrated circuit, etc.

Limit value

Parameter name	Symbol	Normative value	Unit
Off-state repetitive peak blocking voltage	V_{DRM}	≥ 800	V
Reverse repetitive peak blocking voltage	V_{RRM}	≥ 800	V
On-state rms current	$I_{T(RMS)}$	80	A
On-state surging current	I_{TSM}	800	A
Working junction temperature	T_j	-40 ~ 125	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40 ~ 150	$^{\circ}\text{C}$

Electric speciality ($T_j=25^{\circ}\text{C}$)

Parameter name	Symbol	Normative value	Unit	Test conditions
On-state peak voltage	V_{TM}	1.50	V	$I_T=120\text{A}$
Off-state repetitive peak current	I_{DRM}	≤ 1.5	mA	$V_{DRM}=800\text{V}$
Gate triggering current	I_{GT}	≤ 50	mA	$V_{AK}=12\text{V}$ $R_i=10\Omega$
		≤ 50		
		≤ 50		
		≤ 80		
Gate triggering voltage	V_{GT}	≤ 1.3	V	$V_{AK}=12\text{V}$ $R_i=10\Omega$
Maintaining current	I_h	80	mA	
Critical rising rate of off-state voltage	dv/dt	≥ 500	V/ μS	